Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO263(D2PAK) plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series E" is intended for interfacing with low power drivers including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- · Direct interfacing with low power drivers and microcontrollers
- · Good immunity to false turn-on by dV/dt
- · High commutation capability with sensitive gate
- · High voltage capability
- Planar passivated for voltage ruggedness and reliability
- · Surface mountable package
- · Triggering in three quadrants only

3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Va	lues		Unit
Absolute	maximum rating						
V_{DRM}	repetitive peak off-state voltage			8	00		V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 101 °C Fig. 1; Fig. 2; Fig. 3		,	16		А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms Fig. 4; Fig. 5	140			А	
		full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 16.7 \text{ ms}$		1	50		Α
T _j	junction temperature			1	25		°C
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics						
I _{GT} gate trigger current		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 7$		-	-	10	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics				,	•
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	60	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 16 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	5	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 10 \text{ V}/\mu\text{s}; gate open circuit}$	8	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 \text{ °C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 1 \text{ V/}\mu\text{s}; \text{ gate open circuit}$	12	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		. .
2	T2	main terminal 2		T2—T1
3	G	gate		sym051
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
BTA316B-800E	TO263	BTA316B-800E,118	Reel	800	TO263E	26-May-2017

7. Marking

Table 4. Marking codes

Type number	Marking codes
BTA316B-800E	BTA316B-800E

8. Limiting values

Table 5. Limiting valuesIn accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{mb} ≤ 101 °C Fig 1; Fig 2; Fig 3	16	А
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms Fig 4; Fig 5	140	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$; $t_p = 16.7 \text{ms}$	150	А
l ² t	I ² t for fusing	t _P = 10 ms; SIN	98	A ² s
dl _⊤ /dt	rate of rise of on-state current	I _G = 20 mA	100	A/µs
I _{GM}	peak gate current		2	А
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T _{stg}	storage temperature		-40 to 150	°C
T _j	junction temperature		125	°C

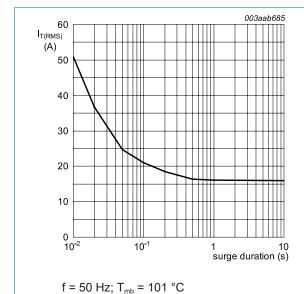


Fig. 1. RMS on-state current as a function of surge duration; maximum values

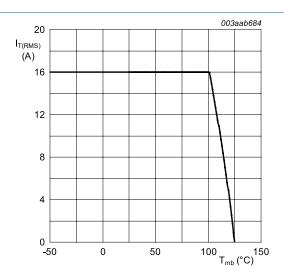
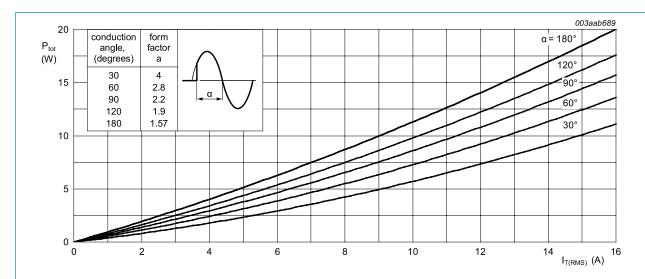


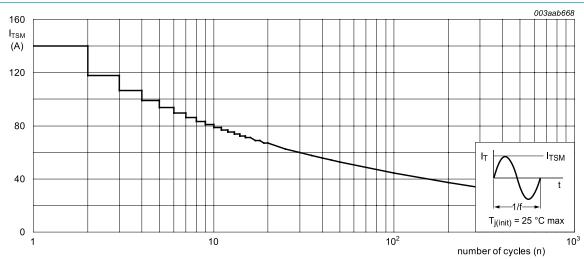
Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



 α = conduction angle

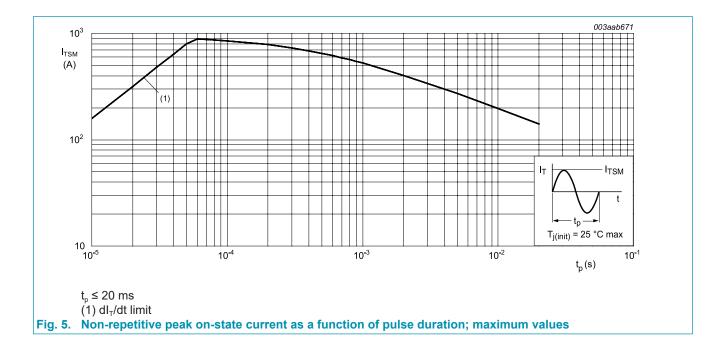
 $a = form factor = I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

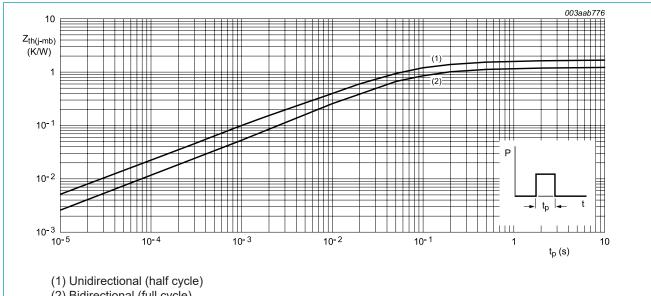
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance	full cycle; Fig 6	-	-	1.2	K/W
	from junction to mounting base	half cycle; <u>Fig 6</u>	-	-	1.7	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board mounted; minimum footprint	-	55	-	K/W



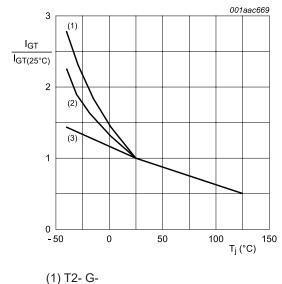
(2) Bidirectional (full cycle)

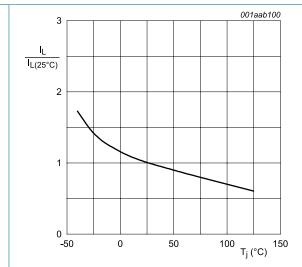
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+; T_j = 25 °C; Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	10	mA
I _L	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2+ G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	30	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 8}}{2}$	-	-	25	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V _T	on-state voltage	I _T = 18 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.3	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.8	1	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
I _D	off-state current	V _D = 800 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 536 V; T_j = 125 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	60	-	-	V/µs
dI _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V; } T_j = 125 \text{ °C; } I_{T(RMS)} = 16 \text{ A;}$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s; (snubberless condition); gate open circuit}$	5	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 10 \text{ V}/\mu\text{s}; gate open circuit}$	8	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 125 ^{\circ}\text{C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 1 \text{ V/}\mu\text{s}; gate open circuit}$	12	-	-	A/ms

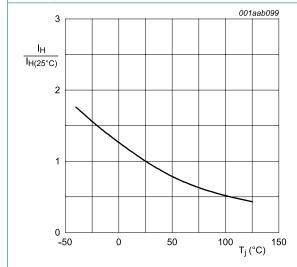


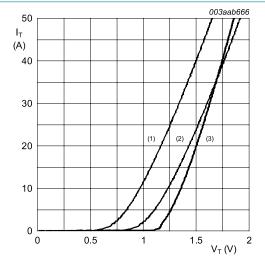


- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature



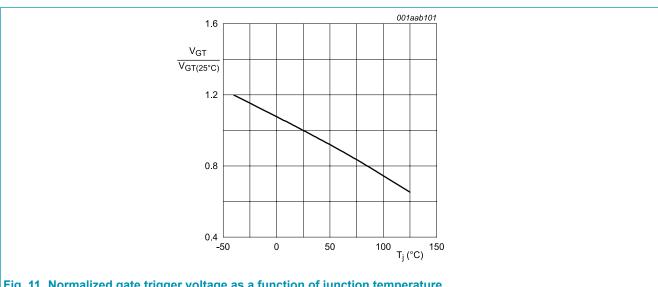




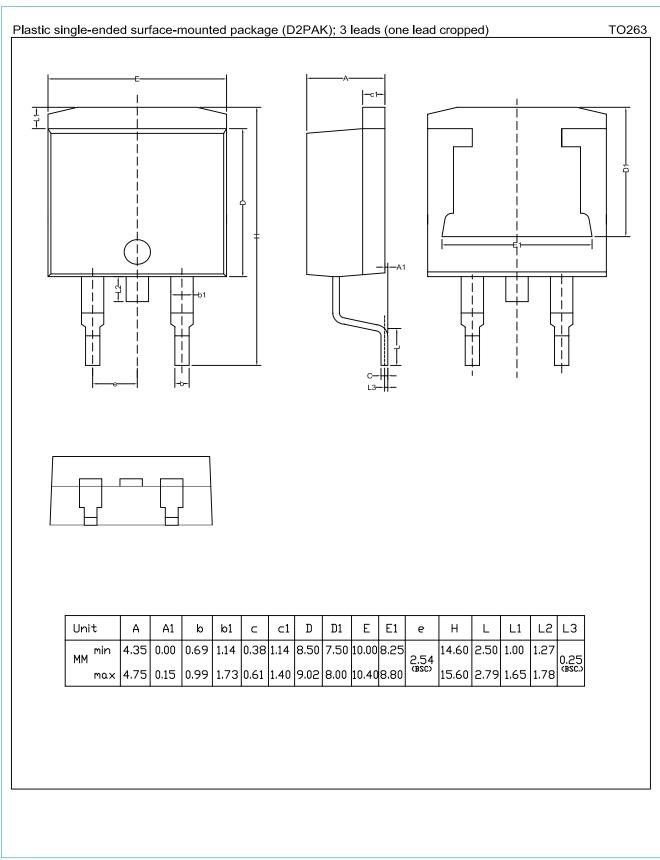
- V_o = 1.024 V; R_s = 0.021 Ω (1) T_j = 125 °C; typical values
- (2) $T_i = 125$ °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 9. Normalized holding current as a function of junction temperature

Fig. 10. On-state current as a function of on-state voltage



11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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